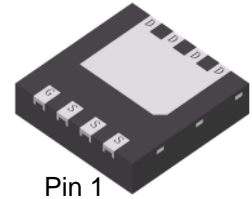


S-LNB8410DT0AG

40V N-Channel MOSFET



Pin 1

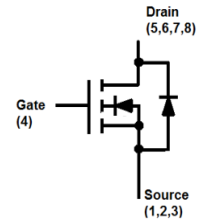
DFN3333-8A

1. FEATURES

- Low thermal impedance.
- Fast switching speed.
- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S-prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.

2. APPLICATIONS

- Power Tools
- UPS
- Motor Control



3. DEVICE MARKING AND RESISTOR VALUES

Device	Marking	Shipping
S-LNB8410DT0AG	LNB8410	2000/Tape&Reel

4. MAXIMUM RATINGS

Parameter		Symbol	Limits	Unit
Drain-to-Source Voltage		VDS	40	V
Gate-to-Source Voltage		VGS	± 20	V
Continuous Drain Current(Note 1)	TA=25°C	ID	12	A
	TA=100°C		7.5	
Pulsed Drain Current (Note 2)		TA=25°C	IDM	48
Continuous Drain Current	TC=25°C	ID	35	A
	TC=100°C		21	
Pulsed Drain Current		TC=25°C	IDM	140
Avalanche Current		IAS	18	A
Avalanche Energy(L=0.1mH)		EAS	16	mJ
Power Dissipation(Note 1)	TA=25°C	PD	2.7	W
	TA=100°C		1.3	
Power Dissipation	TC=25°C	PD	37.5	W
	TC=100°C		19	
Operating Junction and Storage Temperature Range		Tj/Tstg	-55~+175	°C

5. THERMAL CHARACTERISTICS

Parameter	Symbol	Max	Unit
Thermal Resistance,Junction-to-Ambient(Note 1)	RθJA	55	°C/W
Thermal Resistance,Junction-to-Case	RθJC	4	

Note 1.Surface mounted on 1.5 x 1.5 FR4 board using 1 sq in pad, 2 oz Cu.

2.Pulse width limited by maximum junction temperature.

6. ELECTRICAL CHARACTERISTICS(T_J=25°C)

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Static					
Drain to Source Breakdown Voltage (V _{GS} = 0 V, I _D = 250 μA)	BVDSS	40	-	-	V
Gate-Source Threshold Voltage (V _{DS} = V _{GS} , I _D = 250 μA)	V _{GS(th)}	1	1.8	2.5	V
Gate-Body Leakage (V _{DS} = 0 V, V _{GS} = ±20 V)	I _{GSS}	-	-	±100	nA
Zero Gate Voltage Drain Current (V _{DS} = 32 V, V _{GS} = 0 V)	I _{DSS}	-	-	1	μA
Drain-Source On-Resistance(Note 3) (V _{GS} = 10 V, I _D = 20 A) (V _{GS} = 4.5 V, I _D = 20 A)	R _{DS(on)}	-	8 11.5	10 19	mΩ
Dynamic					
Input Capacitance	C _{iss} (V _{DS} = 20 V, V _{GS} = 0 V, f = 1MHz)	C _{iss}	-	690	-
Output Capacitance		C _{oss}	-	229	-
Reverse Transfer Capacitance		C _{rss}	-	12	-
Total Gate Charge	Q _g (V _{DS} = 20 V, V _{GS} = 10 V, I _D = 20 A)	Q _g	-	10	-
Gate-Source Charge		Q _{gs}	-	3	-
Gate-Drain Charge		Q _{gd}	-	2	-
Turn-On Delay Time	t _{d(on)} (V _{DS} = 20 V, I _D = 20 A, V _{GEN} = 10 V, R _{GEN} = 10 Ω)	t _{d(on)}	-	7.4	-
Rise Time		t _r	-	6.4	-
Turn-Off Delay Time		t _{d(off)}	-	23	-
Fall Time		t _f	-	9	-
Diode characteristics					
Continuous Current	I _S	-	-	35	A
Plused Current	I _{SM}	-	-	140	A
Diode Forward Voltage (I _S = 2 A, V _{GS} = 0 V)	V _{SD}	-	0.7	1.2	V
Reverse Recovery Time (V _R =20V, I _F =6A, dI _F /dt=100A/us)	t _{rr}	-	74	-	ns
Reverse Recovery Charge (V _R =20V, I _F =6A, dI _F /dt=100A/us)	Q _{rr}	-	51	-	nC
Reverse Recovery Current (V _R =20V, I _F =6A, dI _F /dt=100A/us)	I _{RRM}	-	1.4	-	A

3. Pulse test: PW ≤ 300us duty cycle ≤ 2%.

7. ELECTRICAL CHARACTERISTICS CURVES

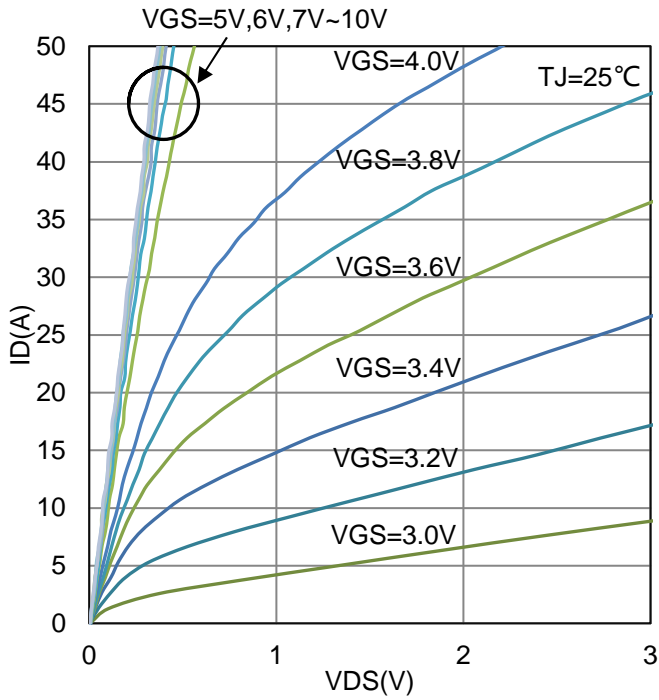


Figure 1.ID vs. VDS

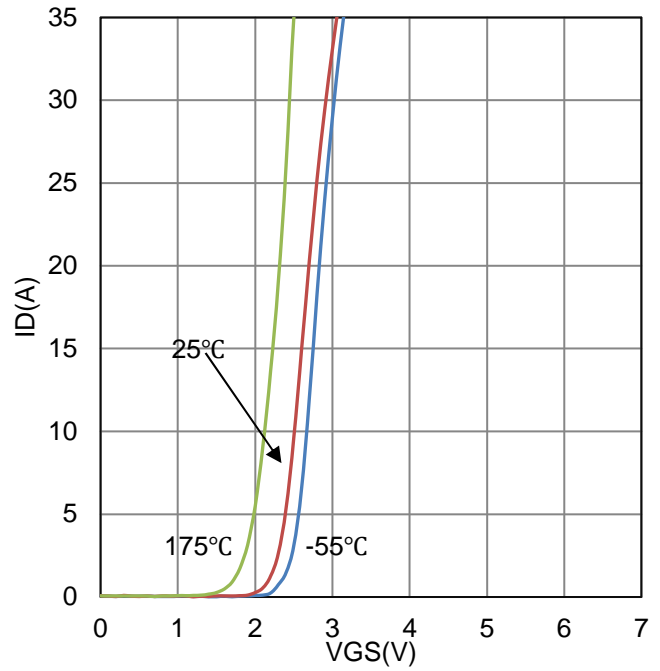


Figure 2.ID vs. VGS

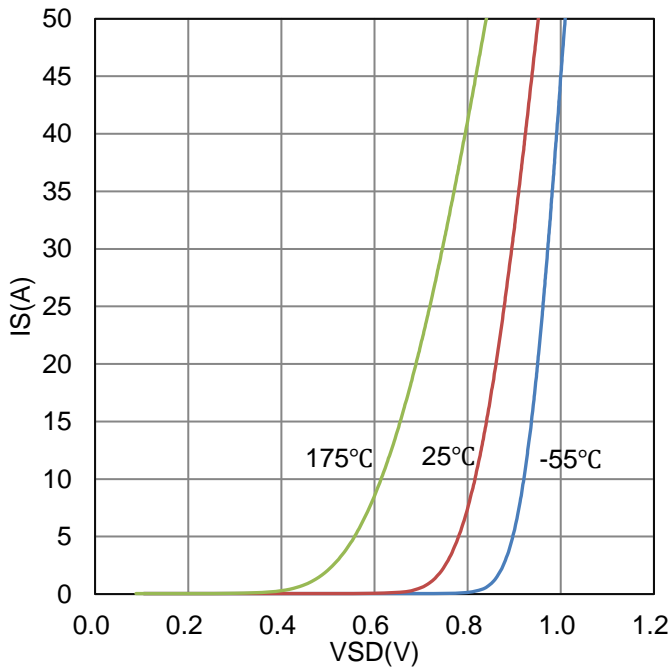


Figure 3.IS vs. VSD

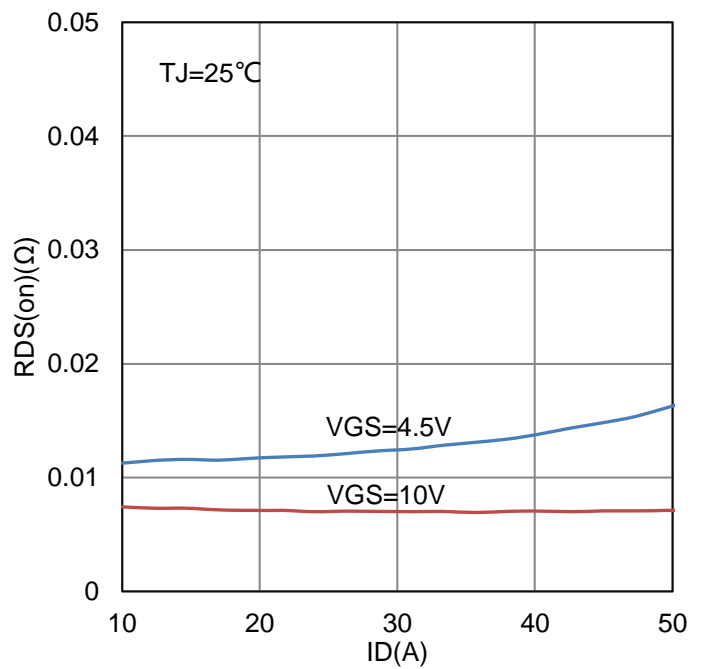


Figure 4.RDS(on) vs. ID

7. ELECTRICAL CHARACTERISTICS CURVES(Con.)

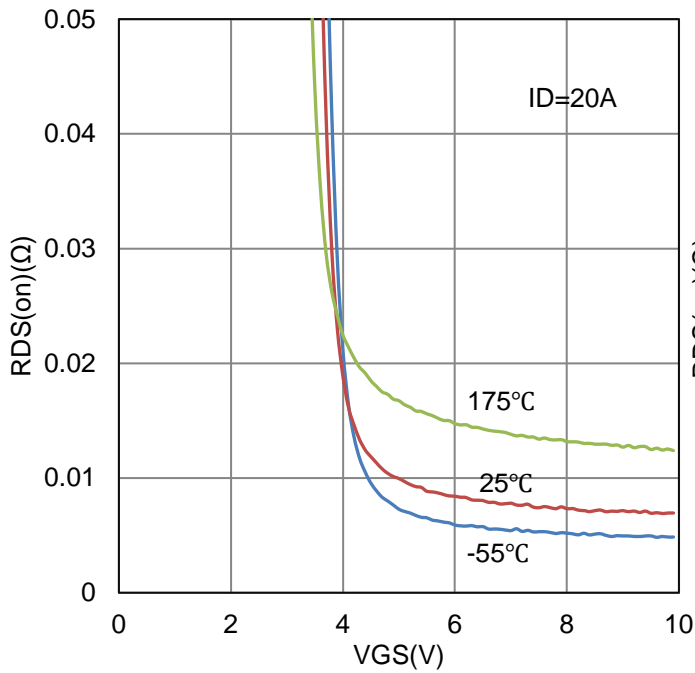


Figure 5. RDS(on) vs. VGS

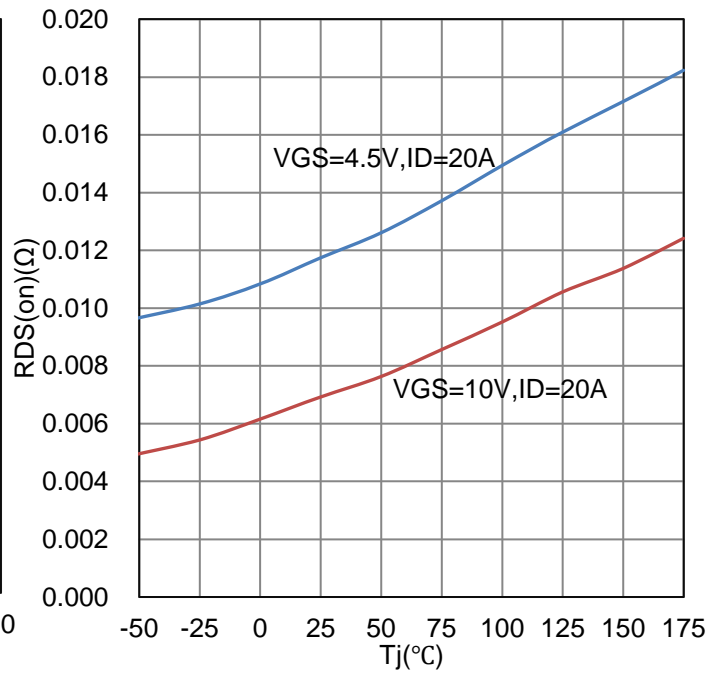


Figure 6. RDS(on) vs. Tj

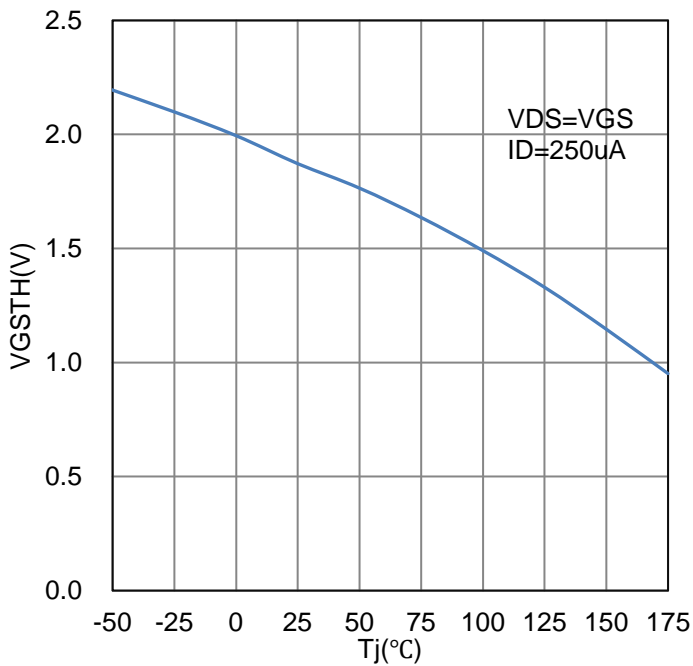


Figure 7. VGStH vs. Tj

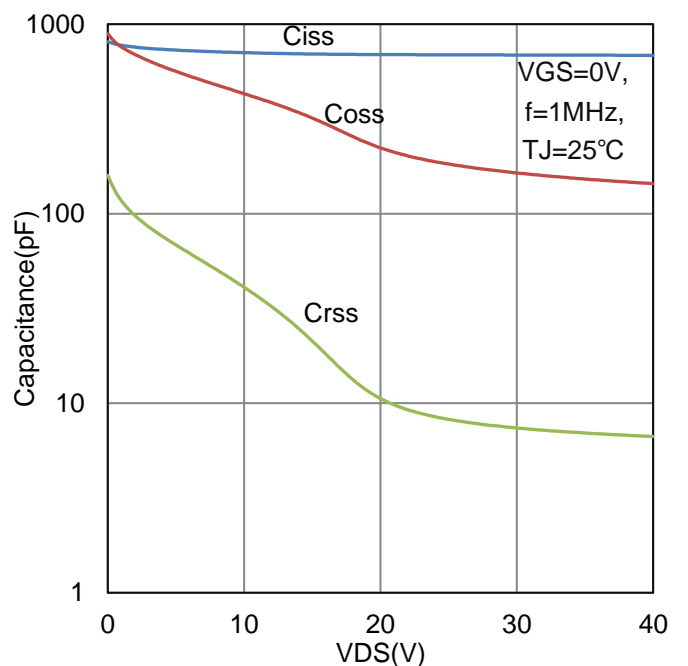


Figure 8. Capacitance

7. ELECTRICAL CHARACTERISTICS CURVES(Con.)

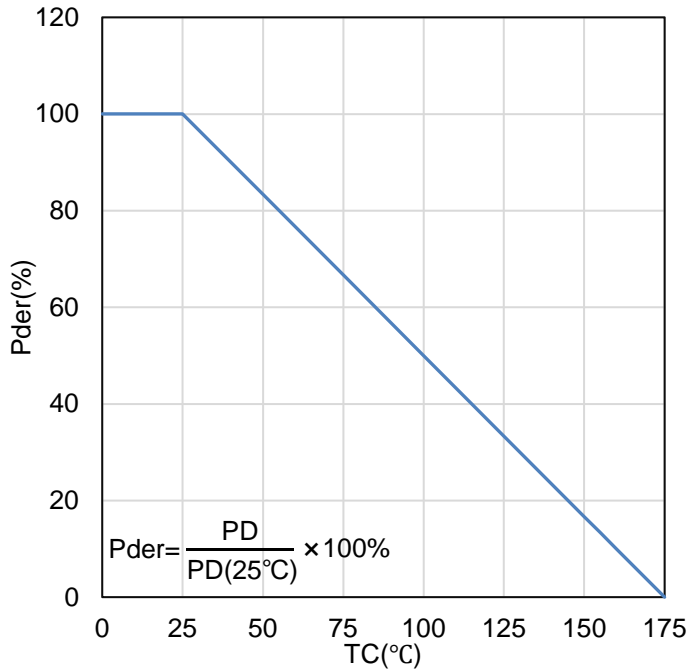


Figure 9. Normalized Derating Curve

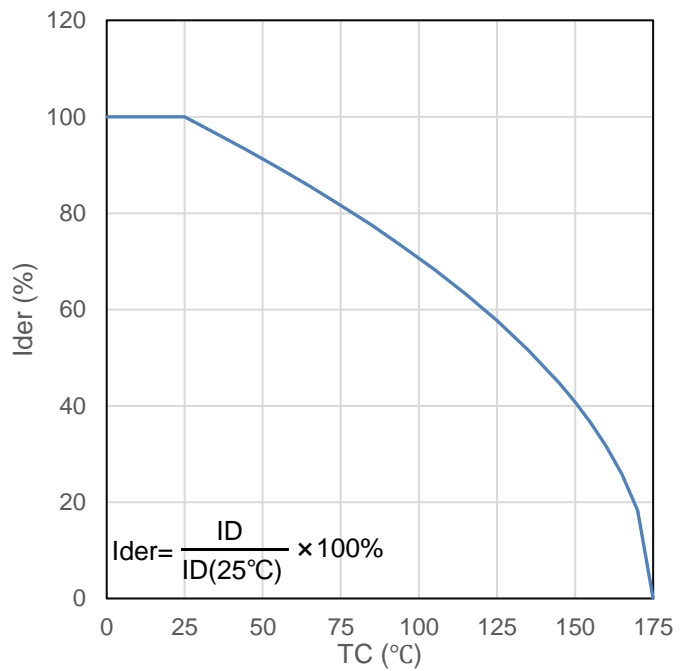


Figure 10. Normalized drain Current

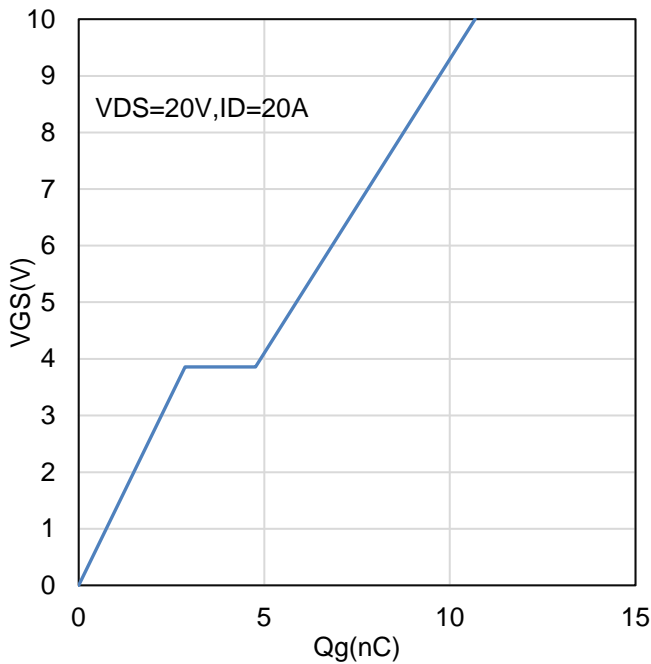


Figure 11. VGS vs. Qg

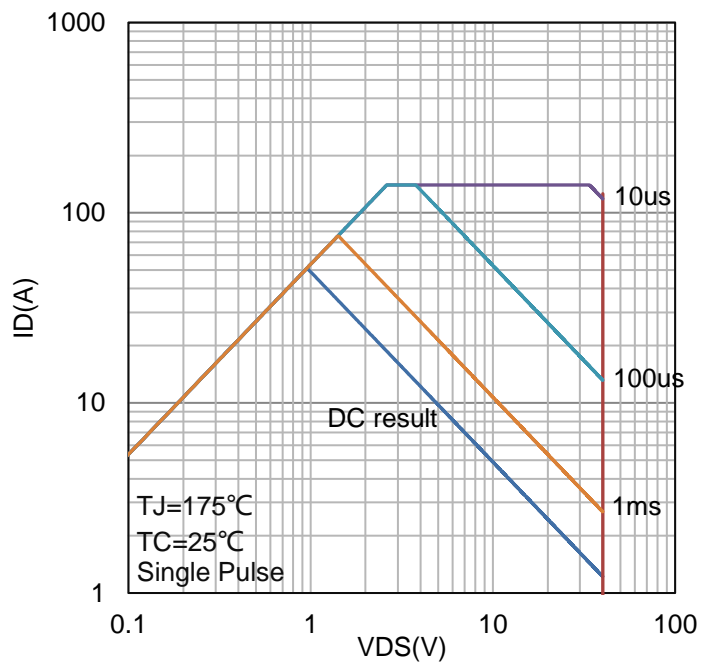


Figure 12. Safe Operating Area

7. ELECTRICAL CHARACTERISTICS CURVES(Con.)

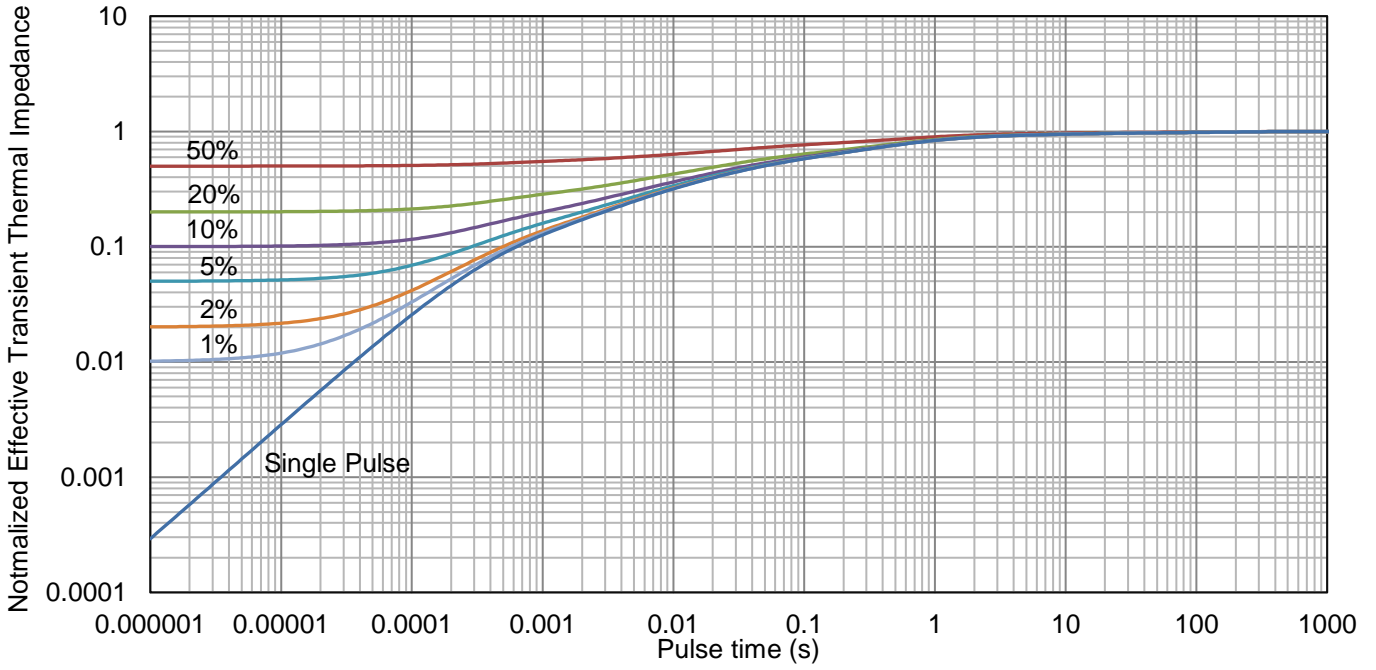
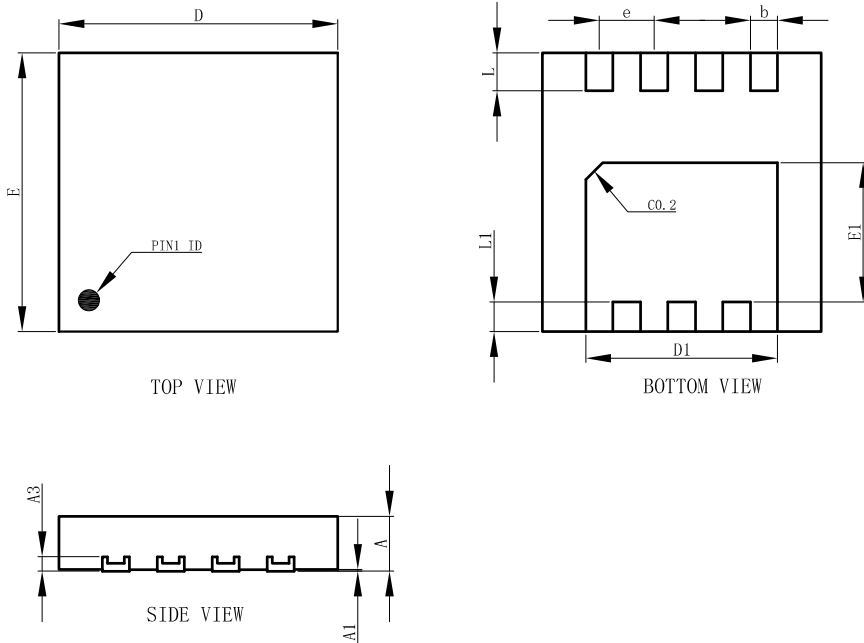


Figure 13. Thermal Response

8. OUTLINE AND DIMENSIONS

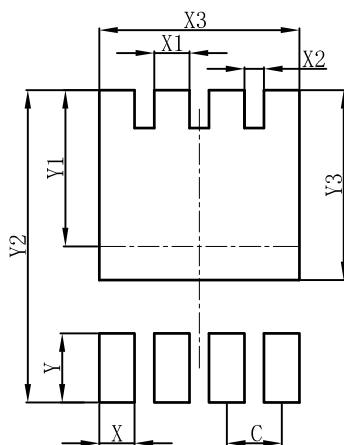
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DFN3333-8A			
DIM	MIN	NOR	MAX
A	0.60	0.65	0.70
A1	0.00	0.03	0.05
b	0.27	0.32	0.37
D	3.25	3.30	3.35
E	3.25	3.30	3.35
D1	2.22	2.27	2.32
E1	1.60	1.65	1.70
e	0.65BSC		
L	0.40	0.45	0.50
L1	0.30	0.35	0.40
A3	0.152REF.		
All Dimensions in mm			

9. SOLDERING FOOTPRINT

DFN3333-8A



DFN3333-8A	
DIM	(mm)
C	0.65
X	0.42
X1	0.42
X2	0.23
X3	2.37
Y	0.70
Y1	1.85
Y2	3.70
Y3	2.25

DISCLAIMER

- Curve guarantee in the specification. The curve of test items with electric parameter is used as quality guarantee. The curve of test items without electric parameter is used as reference only.
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